

Sub A3 C1 3(Amended). The method as described in claim 2, wherein said solar cell comprises silicon.

Sub C1 A7 7(Amended). The method as described in claim 6, further comprising the step of selective KOH etching to remove reactive ion etching induced surface damage.

Sub A5 C1 9(Amended). The method as described in claim 1, wherein the grating comprises rectangular projections.

10(Amended). The method as described in claim 1, wherein the grating comprises triangular projections.

Sub A6 C1 12(Amended). The method as described in claim 2, wherein the grating is chosen to have optimal performance within the solar spectrum.

13(Amended). The method as described in claim 1, further comprising the step of anti-reflection coating the surface of the grating upon which light is incident.

Sub A7 B2 15(Amended). A method for producing a solar cell having increased absorption of light radiation incident on a surface thereof which comprises the steps of: (a) forming a grating on the surface of said solar cell upon which the light is incident; (b) removing surface contamination; (c) forming an n-type junction using gas source doping; and (d) forming n- and p-electrical contacts.

Sub A8 C1 17(Amended). The method as described in claim 16, further comprising the step of removing reactive ion etching-induced surface damage using wet chemical etching.

18(Amended). The method as described in claim 17, wherein said step of wet chemical etching comprises exposing the surface to KOH and nitric acid solutions.

Sub A9 B3 20(Amended). A method for producing a solar cell having increased absorption of light radiation incident on a surface thereof which comprises the steps of: (a) forming a grating on the surface of said solar cell upon which the light is incident; (b) cleaning the surface to remove surface contamination; (c) forming an n-type junction by ion implantation; (d) annealing the solar cell formed thereby; and (e) forming n- and p-electrical contacts.